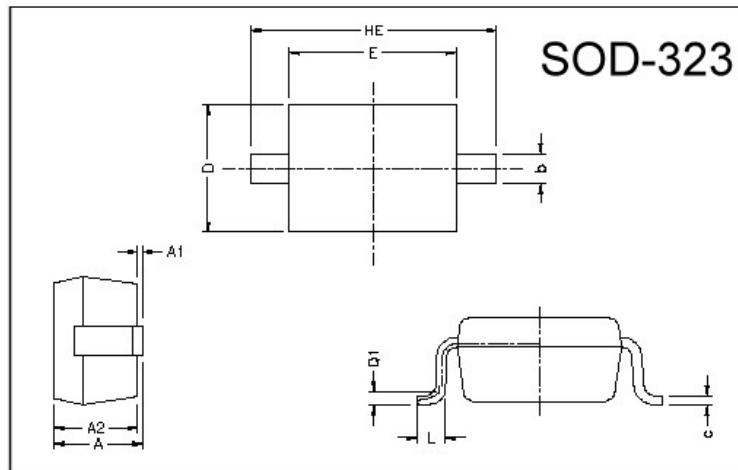


GDMBZ5221B~GDMBZ5270B

Description

ZENER DIODES

Package Dimensions



Marking :			Circuit:		
REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.85	1.05			
A1	0	0.10	L	0.20	0.40
A2	0.80	1.00	b	0.25	0.40
D	1.15	1.45	c	0.10	0.18
E	1.60	1.80			
HE	2.30	2.70	Q1	0.15 BSC.	

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board Ta=25°C, Derate above 25°C	PD	225 1.8	mW mW/°C
Total Device Dissipation Alumina Substrate**TA=25°C, Derate above 25°C	PD	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	R θ JA	417	°C/W
Junction and Storage Temperature	Tj, Tstg	-55 to +150	°C

*FR-5 - 1.0 × 0.75 × 0.062 in. **Alumina-0.4 × 0.3 × 0.024 in. 99.5% alumina.

Thermal Characteristics (VF=0.9V Max @ IF=10mA for all types.)

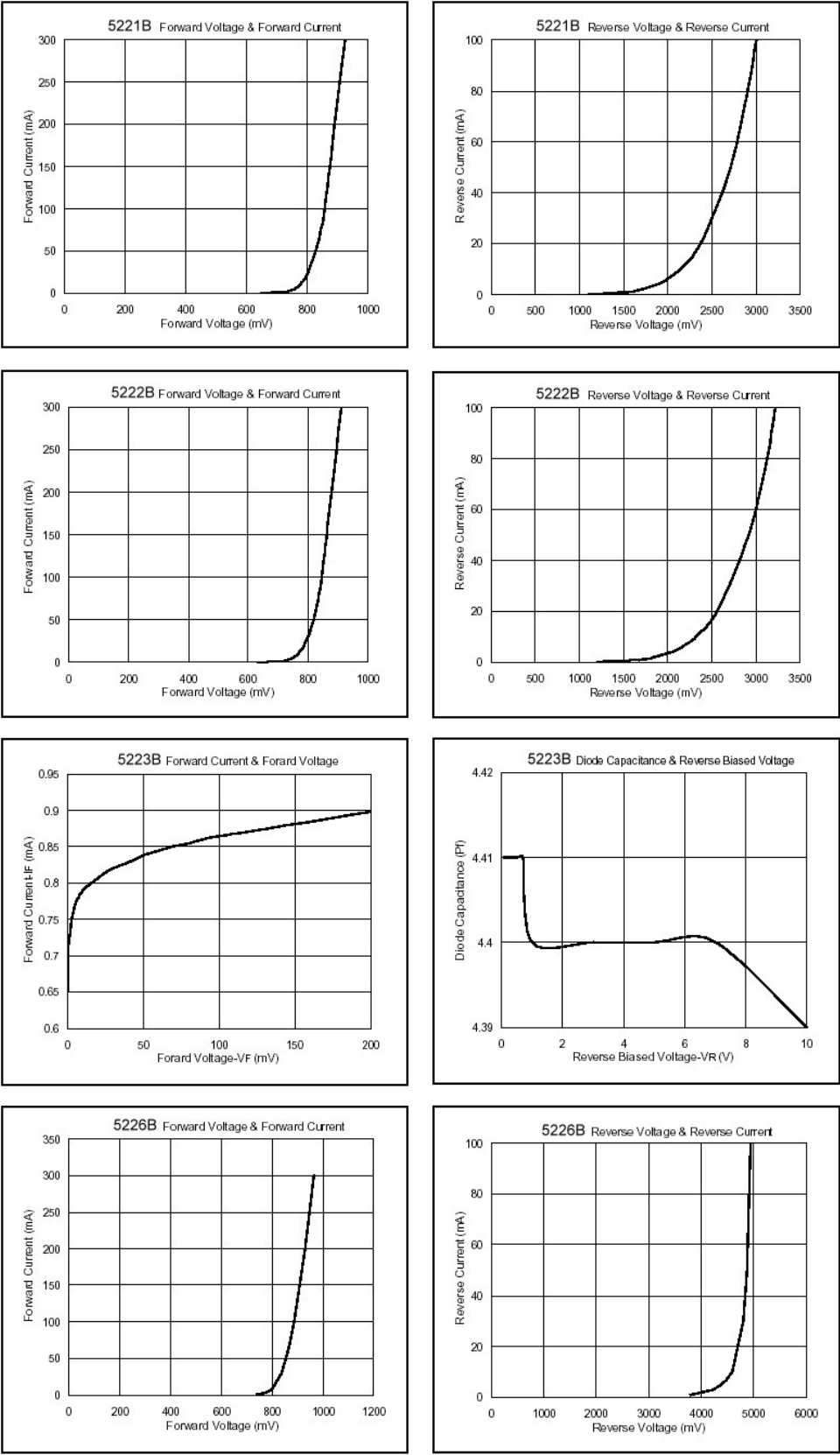
Device	Marking Code	Test Current IZT(mA)	Zener Voltage Vz(V)			ZZK IZ=0.25mA Ω Max	ZZT IZ=IZT Ω Max	Max. Reverse Current	
			Min	Nominal	Max			IR(μA)	@VR(V)
GDMBZ5221B	1A	20	2.280	2.4	2.520	1200	30	100	1.0
GDMBZ5222B	1B	20	2.375	2.5	2.625	1250	30	100	1.0
GDMBZ5223B	1C	20	2.565	2.7	2.835	1300	30	75	1.0
GDMBZ5224B	1D	20	2.660	2.8	2.940	1400	30	75	1.0
GDMBZ5225B	1E	20	2.850	3.0	3.150	1600	29	50	1.0
GDMBZ5226B	8A	20	3.135	3.3	3.465	1600	28	25	1.0
GDMBZ5227B	8B	20	3.420	3.6	3.780	1700	24	15	1.0
GDMBZ5228B	8C	20	3.705	3.9	4.095	1900	23	10	1.0
GDMBZ5229B	8D	20	4.085	4.3	4.515	2000	22	5.0	1.0
GDMBZ5230B	8E	20	4.465	4.7	4.935	1900	19	5.0	2.0
GDMBZ5231B	8F	20	4.845	5.1	5.355	1600	17	5.0	2.0
GDMBZ5232B	8G	20	5.320	5.6	5.880	1600	17	5.0	3.0
GDMBZ5233B	8H	20	5.700	6.0	6.300	1600	7.0	5.0	3.5
GDMBZ5234B	8J	20	5.890	6.2	6.510	1000	7.0	5.0	4.0
GDMBZ5235B	8K	20	6.460	6.8	7.140	750	5.0	3.0	5.0
GDMBZ5236B	8L	20	7.125	7.5	7.875	500	6.0	3.0	6.0
GDMBZ5237B	8M	20	7.790	8.2	8.610	500	8.0	3.0	6.5
GDMBZ5238B	8N	20	8.265	8.7	9.135	600	8.0	3.0	6.5
GDMBZ5239B	8P	20	8.645	9.1	9.555	600	10	3.0	7.0
GDMBZ5240B	8Q	20	9.500	10	10.500	600	17	3.0	8.0

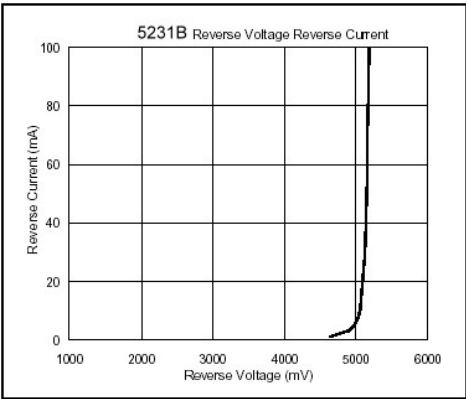
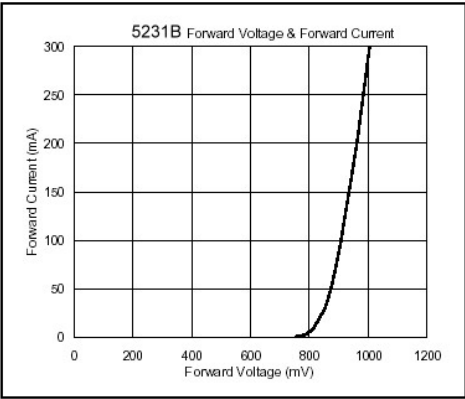
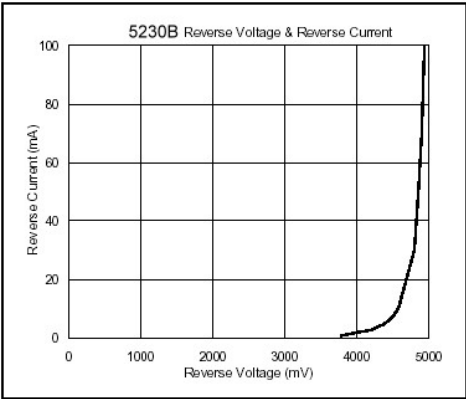
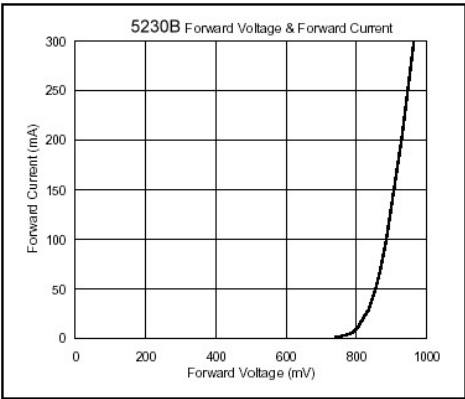
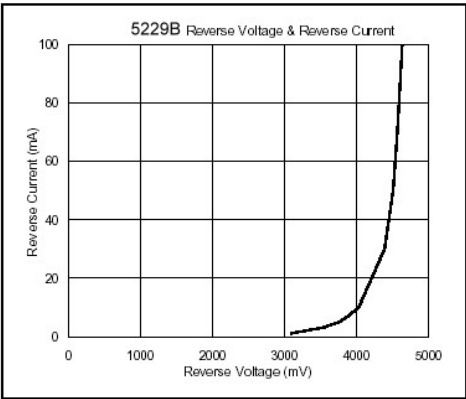
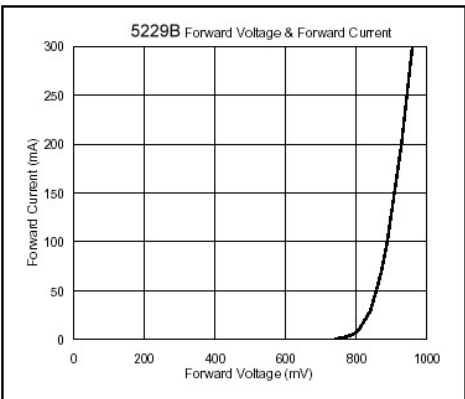
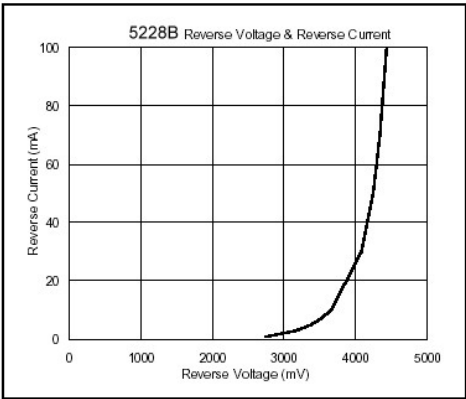
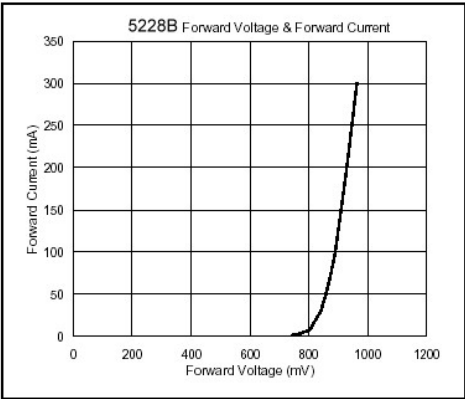
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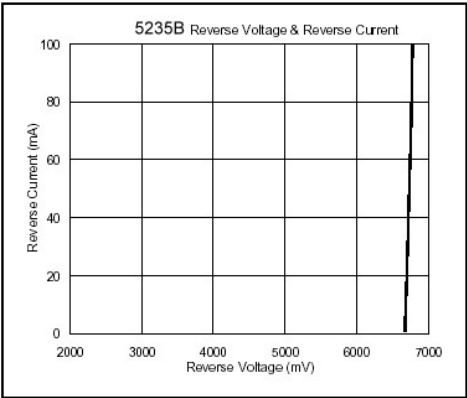
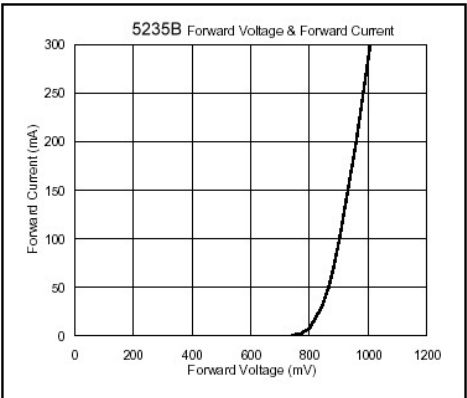
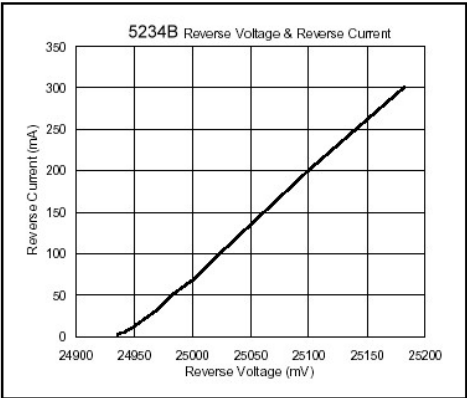
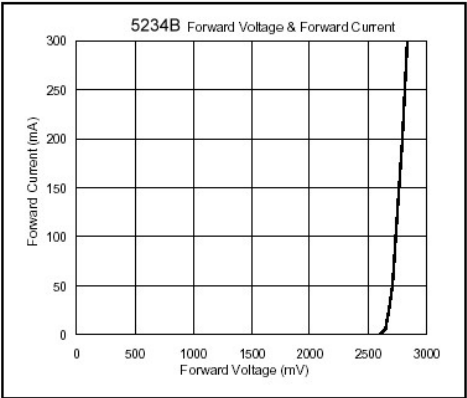
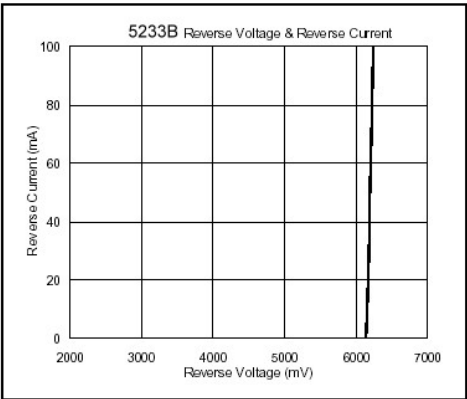
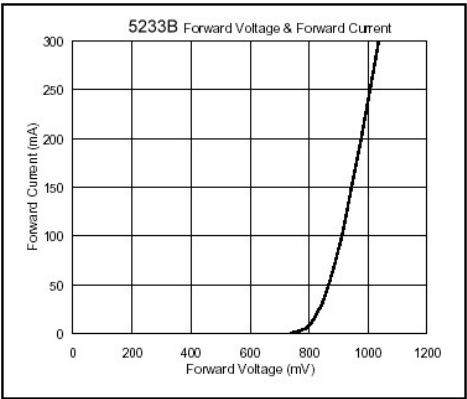
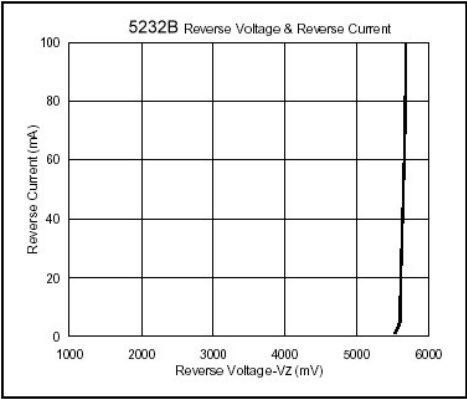
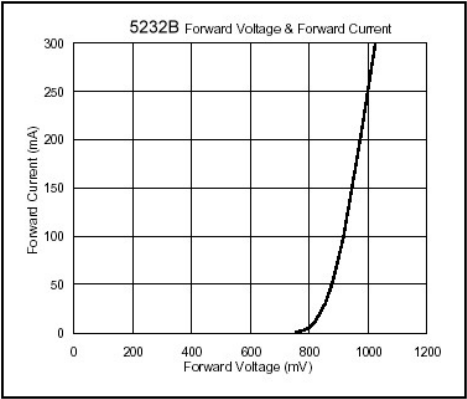
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REVISED DATE :

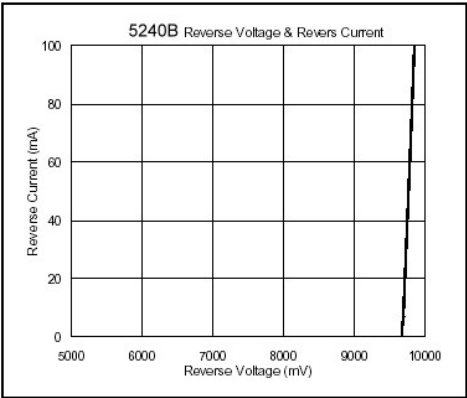
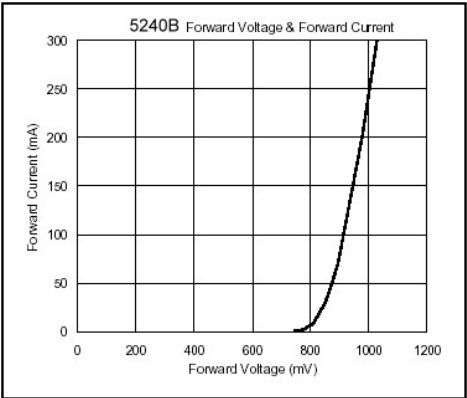
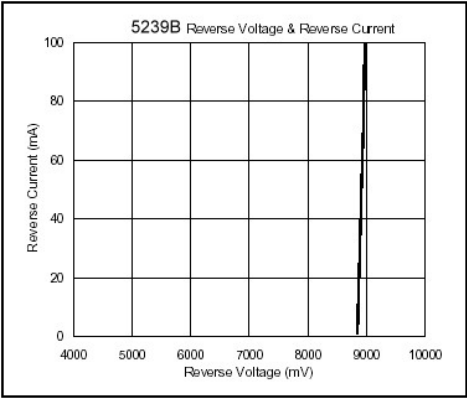
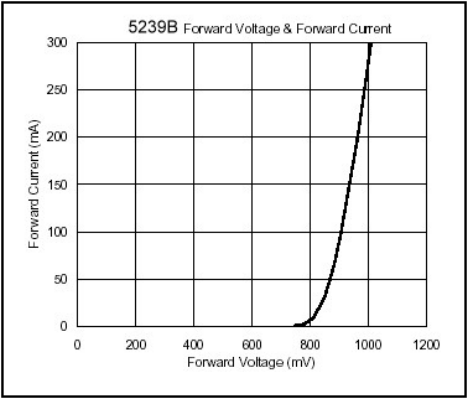
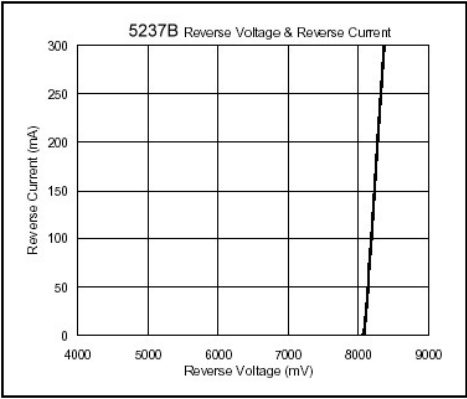
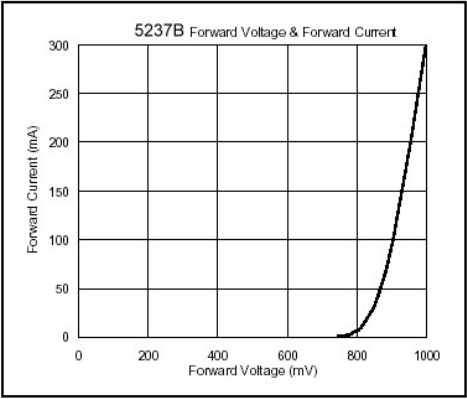
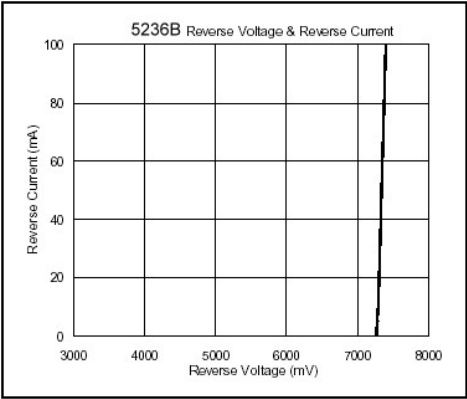
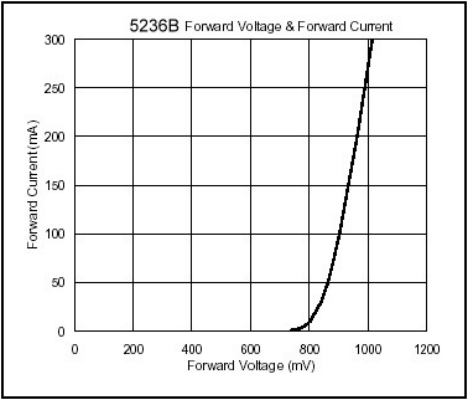
Device	Marking Code	Test Current IZT(mA)	Zener Voltage Vz(V)			ZZK IZ=0.25mA Ω Max	ZZT IZ=IZT Ω Max	Max. Reverse Current	
			Min	Nominal	Max			IR(μA)	@VR(V)
GDMBZ5241B	8R	20	10.450	11	11.550	600	22	2.0	8.4
GDMBZ5242B	8S	20	11.400	12	12.600	600	30	1.0	9.1
GDMBZ5243B	8T	9.5	12.350	13	13.650	600	13	0.5	9.9
GDMBZ5244B	8U	9.0	13.300	14	14.700	600	15	0.1	10
GDMBZ5245B	8V	8.5	14.250	15	15.750	600	16	0.1	11
GDMBZ5246B	8W	7.8	15.200	16	16.800	600	17	0.1	12
GDMBZ5247B	8X	7.4	16.150	17	17.850	600	19	0.1	13
GDMBZ5248B	8Y	7.0	17.100	18	18.900	600	21	0.1	14
GDMBZ5249B	8Z	6.6	18.050	19	19.950	600	23	0.1	14
GDMBZ5250B	2A	6.2	19.000	20	21.000	600	25	0.1	15
GDMBZ5251B	2B	5.6	20.900	22	23.100	600	29	0.1	17
GDMBZ5252B	2C	5.2	22.800	24	25.200	600	33	0.1	18
GDMBZ5253B	2D	5.0	23.750	25	26.250	600	35	0.1	19
GDMBZ5254B	2E	4.6	25.650	27	28.350	600	41	0.1	21
GDMBZ5255B	2F	4.5	26.600	28	29.400	600	44	0.1	21
GDMBZ5256B	2G	4.2	28.500	30	31.500	600	49	0.1	23
GDMBZ5257B	2H	3.8	31.350	33	34.650	700	58	0.1	25
GDMBZ5258B	2J	3.4	34.200	36	37.800	700	70	0.1	27
GDMBZ5259B	2K	3.2	37.050	39	40.950	800	80	0.1	30
GDMBZ5260B	2L	3.0	40.850	43	45.150	900	93	0.1	33
GDMBZ5261B	2M	2.7	44.650	47	49.350	1000	105	0.1	36
GDMBZ5262B	2N	2.5	48.450	51	53.550	1100	125	0.1	39
GDMBZ5263B	2P	2.2	53.200	56	58.800	1300	150	0.1	43
GDMBZ5264B	2Q	2.1	57.000	60	63.000	1400	170	0.1	46
GDMBZ5265B	2R	2.0	58.900	62	65.100	1400	185	0.1	47
GDMBZ5266B	2S	1.8	64.600	68	71.400	1600	230	0.1	52
GDMBZ5267B	2T	1.7	71.250	75	78.750	1700	270	0.1	56
GDMBZ5268B	2U	1.5	77.900	82	86.100	2000	330	0.1	62
GDMBZ5269B	2V	1.4	82.650	87	91.350	2200	370	0.1	68
GDMBZ5270B	2W	1.4	86.450	91	95.550	2300	400	0.1	69

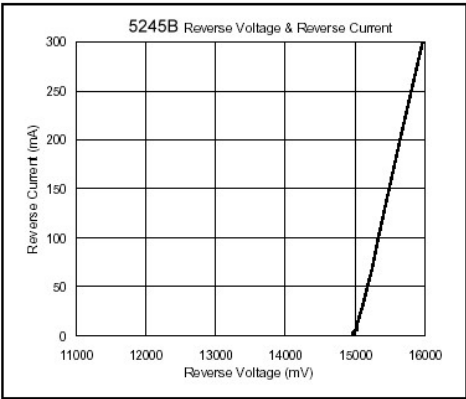
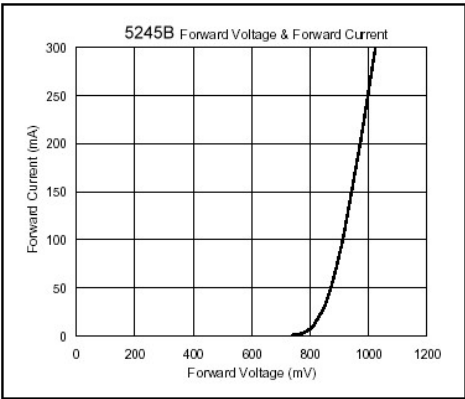
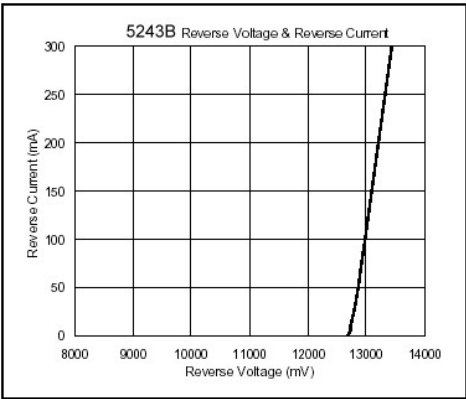
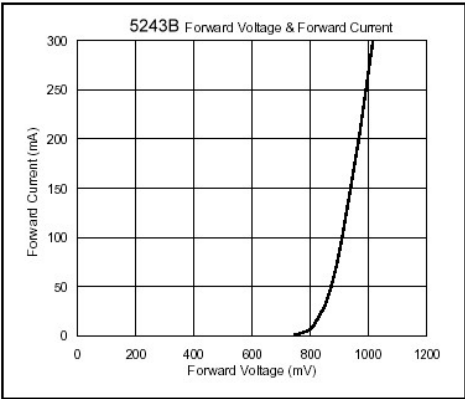
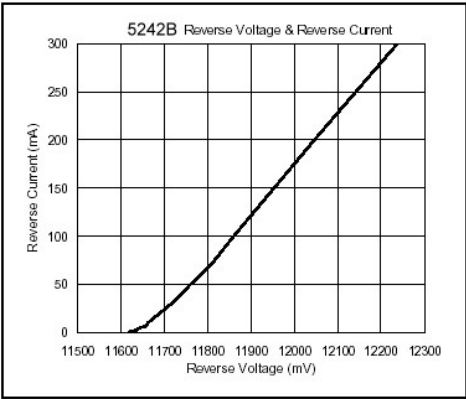
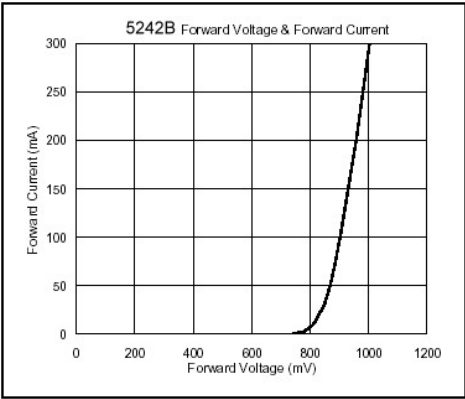
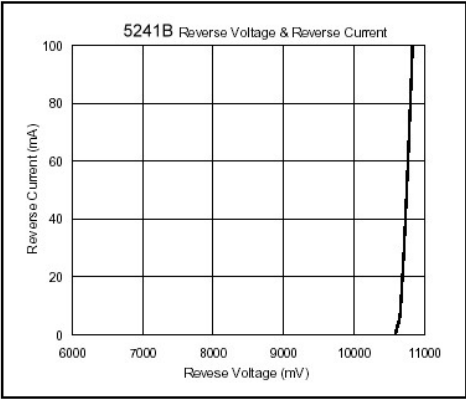
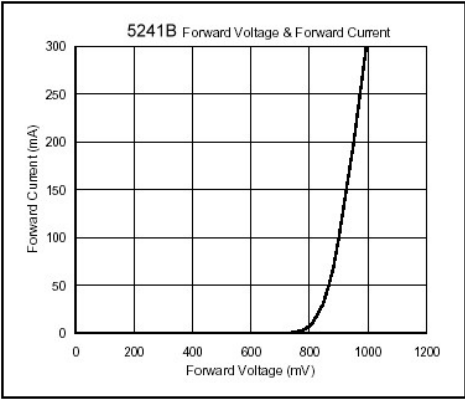
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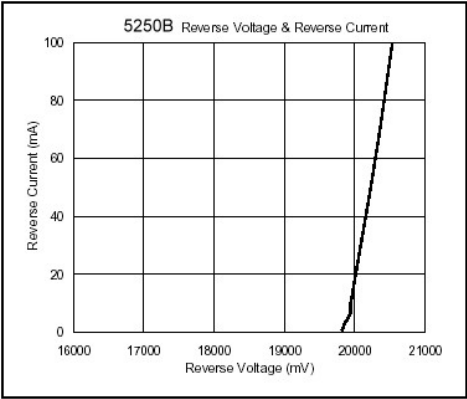
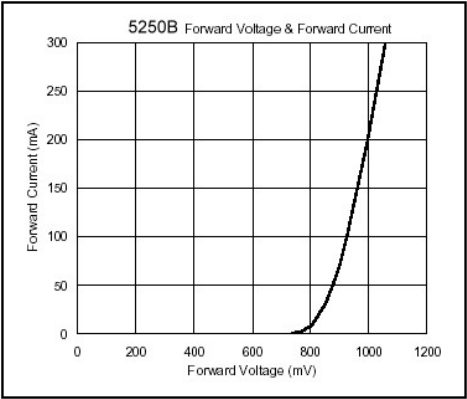
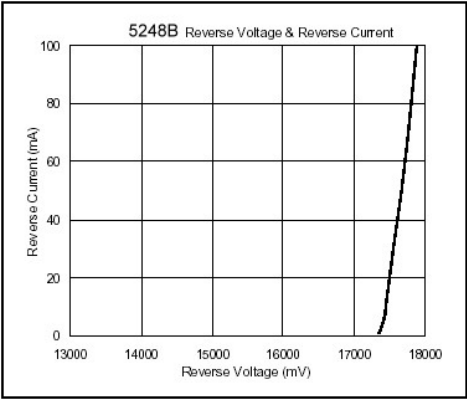
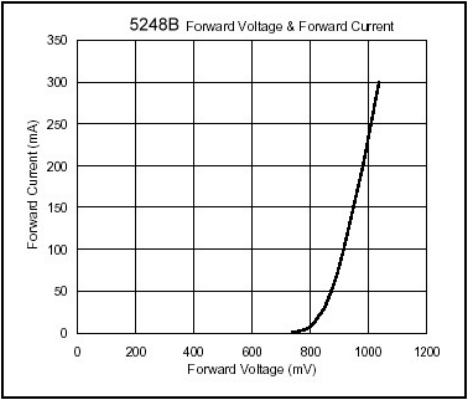
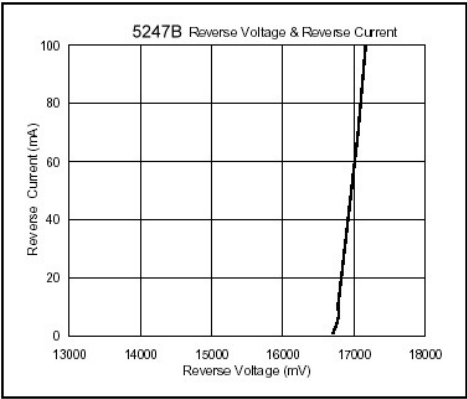
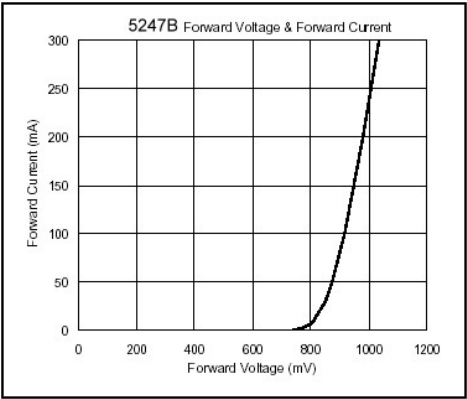
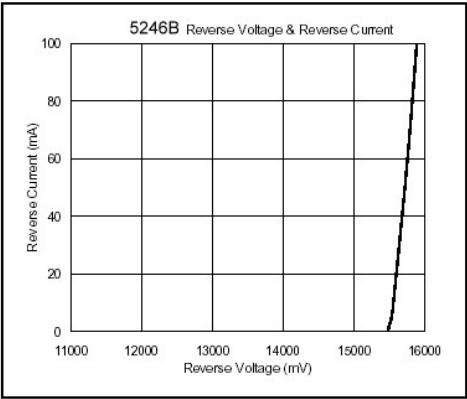
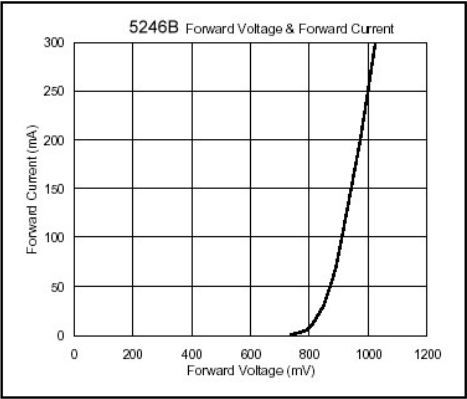


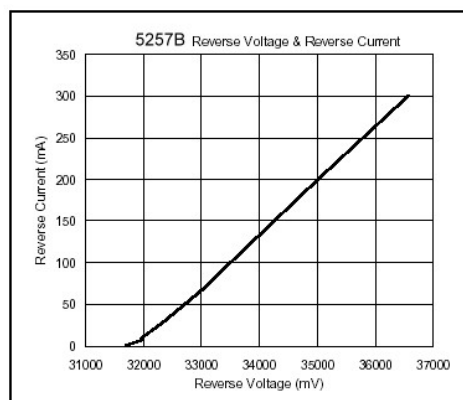
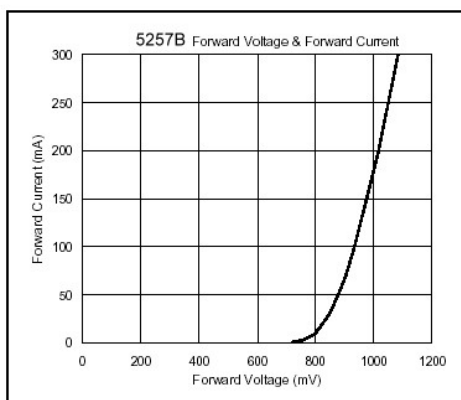
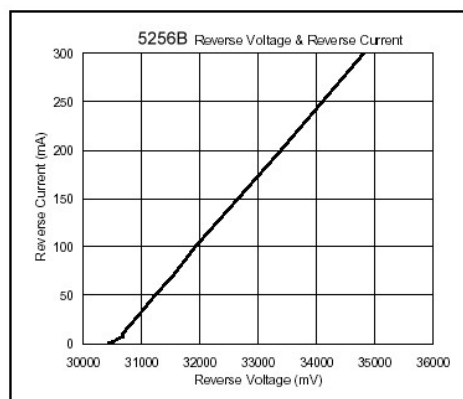
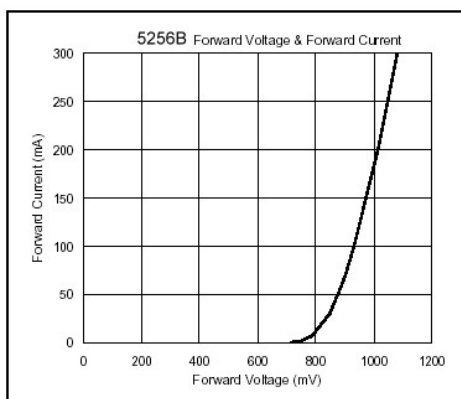
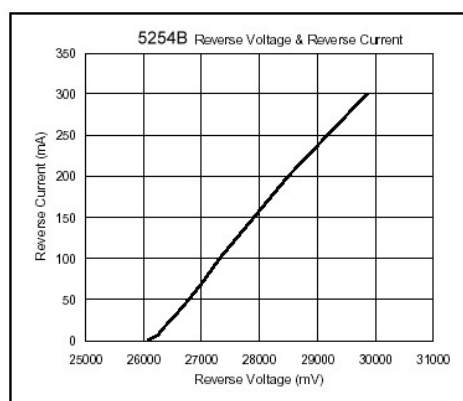
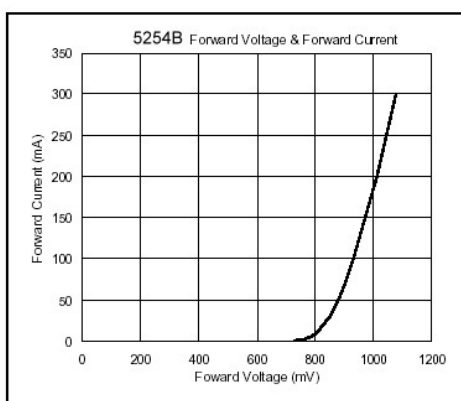
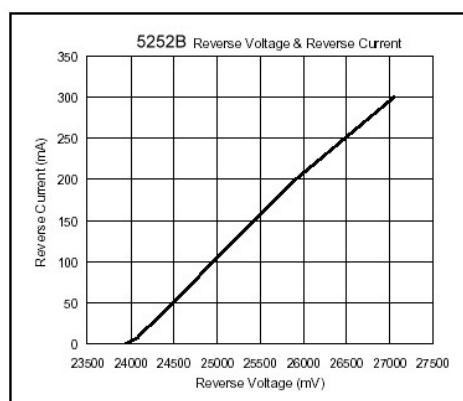
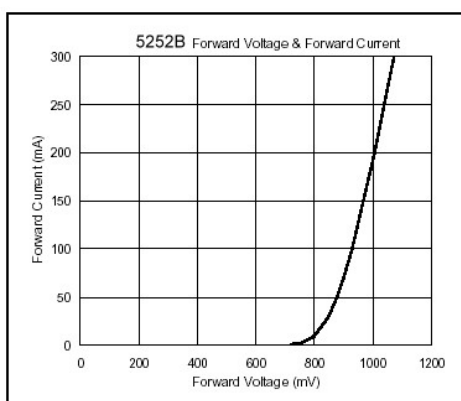










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